

In re application of: Ki-Yeon Park, et al. Conf. No. 8248  
Serial No. 10/713,577 Examiner: Nhu, David  
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For: CAPACITOR OF SEMICONDUCTOR MEMORY DEVICE THAT HAS  
COMPOSITE  $\text{Al}_2\text{O}_3/\text{HfO}_2$  DIELECTRIC LAYER AND METHOD OF  
MANUFACTURING THE SAME

INFORMATION DISCLOSURE CITATION  
FORM PTO-1449 (Modified)

U.S. PATENT DOCUMENTS

| Exam<br>Init | Ref | Document<br>Number | Issue<br>Date | Name             | Class | Sub<br>Class |
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Examiner: *[Signature]*

Date Considered: 2/28/05